

## **KSA709**

### **High Voltage Amplifier**

- Collector-Base Voltage: V<sub>CBO</sub>= -160V
  Collector-Base Voltage: V<sub>CBO</sub>= -160V
- Collector Power Dissipation : P<sub>C</sub>=800mW
- Complement to KSC1009
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



## **PNP Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>CBO</sub>	Collector-Base Voltage	-160	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-150	V
V <sub>EBO</sub>	Emitter-Base Voltage	-8	V
I <sub>C</sub>	Collector Current	-700	mA
P <sub>C</sub>	Collector Power Dissipation	800	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -100 \mu A, I_E = 0$	-160			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10mA, I <sub>B</sub> =0	-150			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = -100 \mu A, I_C = 0$	-8			V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = -100V, I <sub>E</sub> =0			-0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ = -5V, $I_{C}$ =0			-0.1	μΑ
h <sub>FE</sub>	* DC Current Gain	$V_{CE}$ = -2V, $I_{C}$ = -50mA	70		400	
V <sub>CE</sub> (sat)	* Collector-Emitter Saturation Voltage	$I_C = -200 \text{mA}, I_B = -20 \text{mA}$		-0.3	-0.4	V
V <sub>BE</sub> (sat)	* Base-Emitter Saturation Voltage	$I_{C}$ = -200mA, $I_{B}$ = -20mA		-0.9	-1.0	V
f <sub>T</sub>	Current Gain Bandwidth Product	$V_{CE}$ = -10V, $I_{C}$ = -50mA		50		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = -10V, I <sub>E</sub> =0, f=1MHz			10	pF

<sup>\*</sup> Pulse Test: PW≤350μs, Duty cycle≤2%

## **h**<sub>FE</sub> Classification

Classification	0	Y	G
h <sub>FE</sub>	70 ~ 140	120 ~ 240	200 ~ 400

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# **Typical Characteristics**

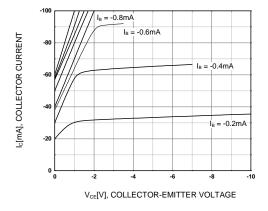


Figure 1. Static Characteristic

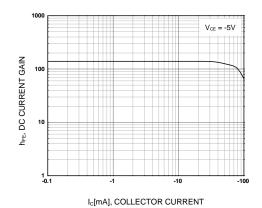


Figure 2. DC current Gain

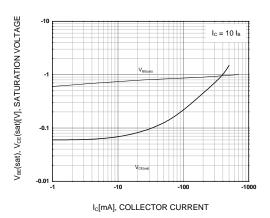


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

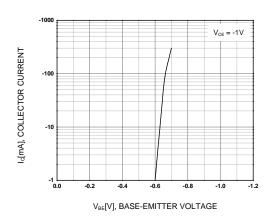


Figure 4. Base-Emitter On Voltage

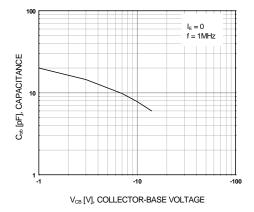
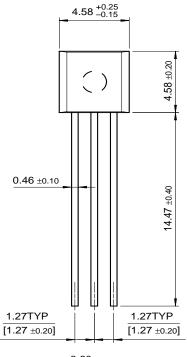


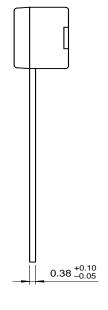
Figure 5. Collector Output Capacitance

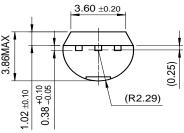
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# **Package Dimensions**

TO-92







Dimensions in Millimeters

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